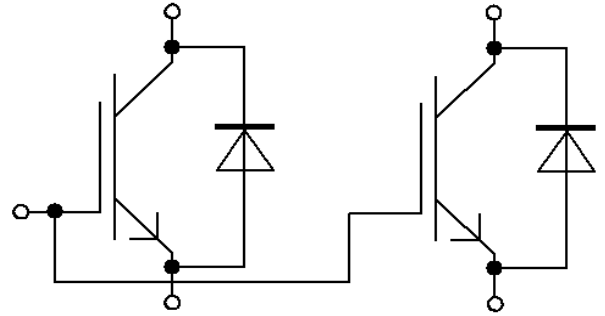


高绝缘等级模块 采用第三代沟槽栅/场终止IGBT3和第三代发射极控制二极管
 high insulated module with Trench/Fieldstop IGBT3 and Emitter Controlled 3 diode



$V_{CES} = 4500V$
 $I_{C\ nom} = 800A / I_{CRM} = 1600A$

潜在应用

- 中压变流器
- 多电平逆变器
- 大功率变流器
- 牵引变流器
- 电机传动

Potential Applications

- Medium voltage converters
- Multi level inverter
- High power converters
- Traction drives
- Motor drives

电气特性

- V_{CESat} 带正温度系数
- 低 V_{CESat}
- 沟槽栅IGBT3
- 高动态坚固性
- 高直流电压稳定性
- 高短路能力

Electrical Features

- V_{CESat} with positive temperature coefficient
- Low V_{CESat}
- Trench IGBT 3
- High dynamic robustness
- High DC stability
- High short-circuit capability

机械特性

- 加强绝缘封装, 10.4kV 交流 10秒第二
- 封装的 CTI > 600
- 碳化硅铝 (AlSiC) 基板提供更高的温度循环能力
- 绝缘的基板
- 高爬电距离和电气间隙

Mechanical Features

- Package with enhanced insulation of 10.4kV AC 10s
- Package with CTI > 600
- AlSiC base plate for increased thermal cycling capability
- Isolated base plate
- High creepage and clearance distances

Module Label Code

Barcode Code 128



DMX - Code



Content of the Code

Content of the Code	Digit
Module Serial Number	1 - 5
Module Material Number	6 - 11
Production Order Number	12 - 19
Datecode (Production Year)	20 - 21
Datecode (Production Week)	22 - 23

IGBT, 逆变器 / IGBT, Inverter

最大额定值 / Maximum Rated Values

集电极 - 发射极电压 Collector-emitter voltage	$T_{vj} = -40^{\circ}\text{C}$ $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	V_{CES}	4500 4500 4500	V
连续集电极直流电流 Continuous DC collector current	$T_C = 80^{\circ}\text{C}, T_{vj\max} = 150^{\circ}\text{C}$	$I_{C\text{nom}}$	800	A
集电极重复峰值电流 Repetitive peak collector current	$t_P = 1\text{ ms}$	I_{CRM}	1600	A
栅极 - 发射极峰值电压 Gate-emitter peak voltage		V_{GES}	+/-20	V

特征值 / Characteristic Values

			min.	typ.	max.	
集电极 - 发射极饱和电压 Collector-emitter saturation voltage	$I_C = 800\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 800\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	$V_{CE\text{sat}}$	2,50 3,10	2,85 3,70	V V
栅极阈值电压 Gate threshold voltage	$I_C = 70,5\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$		V_{GEth}	5,40	6,00	6,60 V
栅极电荷 Gate charge	$V_{GE} = -15\text{ V} \dots +15\text{ V}, V_{CE} = 2800\text{ V}$		Q_G	26,5		μC
内部栅极电阻 Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		R_{Gint}	1,1		Ω
输入电容 Input capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{ies}	185		nF
反向传输电容 Reverse transfer capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{res}	3,10		nF
集电极-发射极截止电流 Collector-emitter cut-off current	$V_{CE} = 4500\text{ V}, V_{GE} = 0\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{CES}		5,0	mA
栅极-发射极漏电流 Gate-emitter leakage current	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{GES}		400	nA
开通延迟时间(电感负载) Turn-on delay time, inductive load	$I_C = 800\text{ A}, V_{CE} = 2800\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 2,4\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	t_{don}	0,75 0,75		μs μs
上升时间(电感负载) Rise time, inductive load	$I_C = 800\text{ A}, V_{CE} = 2800\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 2,4\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	t_r	0,30 0,30		μs μs
关断延迟时间(电感负载) Turn-off delay time, inductive load	$I_C = 800\text{ A}, V_{CE} = 2800\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 7,5\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	t_{doff}	6,60 6,90		μs μs
下降时间(电感负载) Fall time, inductive load	$I_C = 800\text{ A}, V_{CE} = 2800\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 7,5\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	t_f	0,35 0,45		μs μs
开通损耗能量(每脉冲) Turn-on energy loss per pulse	$I_C = 800\text{ A}, V_{CE} = 2800\text{ V}, L_S = 95\text{ nH}$ $V_{GE} = \pm 15\text{ V}, di/dt = 3300\text{ A}/\mu\text{s}$ $R_{Gon} = 1,0\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	E_{on}	3100 4100		mJ mJ
关断损耗能量(每脉冲) Turn-off energy loss per pulse	$I_C = 800\text{ A}, V_{CE} = 2800\text{ V}, L_S = 95\text{ nH}$ $V_{GE} = \pm 15\text{ V}, du/dt = 2000\text{ V}/\mu\text{s}$ $R_{Goff} = 7,5\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	E_{off}	2800 3400		mJ mJ
短路数据 SC data	$V_{GE} \leq 15\text{ V}, V_{CC} = 2800\text{ V}$ $V_{CE\max} = V_{CES} - L_{SCE} \cdot di/dt$ $t_P \leq 10\ \mu\text{s}, T_{vj} = 125^{\circ}\text{C}$		I_{SC}	4600		A
结 - 外壳热阻 Thermal resistance, junction to case	每个 IGBT / per IGBT		R_{thJC}		11,1	K/kW
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个 IGBT / per IGBT $\lambda_{\text{Paste}} = 1\text{ W}/(\text{m}\cdot\text{K})$ / $\lambda_{\text{grease}} = 1\text{ W}/(\text{m}\cdot\text{K})$		R_{thCH}	13,5		K/kW
在开关状态下温度 Temperature under switching conditions			$T_{vj\text{op}}$	-50	125	$^{\circ}\text{C}$

二极管, 逆变器 / Diode, Inverter 最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	$T_{vj} = -40^{\circ}\text{C}$ $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	V_{RRM}	4500 4500 4500	V
连续正向直流电流 Continuous DC forward current		I_F	800	A
正向重复峰值电流 Repetitive peak forward current	$t_p = 1 \text{ ms}$	I_{FRM}	1600	A
I^2t -值 I^2t - value	$V_R = 0 \text{ V}$, $t_p = 10 \text{ ms}$, $T_{vj} = 125^{\circ}\text{C}$	I^2t	255	kA^2s
最大损耗功率 Maximum power dissipation	$T_{vj} = 125^{\circ}\text{C}$	P_{RQM}	1600	kW
最小开通时间 Minimum turn-on time		$t_{on \text{ min}}$	10,0	μs

特征值 / Characteristic Values

			min.	typ.	max.	
正向电压 Forward voltage	$I_F = 800 \text{ A}$, $V_{GE} = 0 \text{ V}$ $I_F = 800 \text{ A}$, $V_{GE} = 0 \text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	V_F	2,50 2,50	3,10 3,00	V V
反向恢复峰值电流 Peak reverse recovery current	$I_F = 800 \text{ A}$, $-di_F/dt = 3300 \text{ A}/\mu\text{s}$ ($T_{vj}=125^{\circ}\text{C}$) $V_R = 2800 \text{ V}$ $V_{GE} = -15 \text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	I_{RM}	1000 1150		A A
恢复电荷 Recovered charge	$I_F = 800 \text{ A}$, $-di_F/dt = 3300 \text{ A}/\mu\text{s}$ ($T_{vj}=125^{\circ}\text{C}$) $V_R = 2800 \text{ V}$ $V_{GE} = -15 \text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	Q_r	770 1400		μC μC
反向恢复损耗 (每脉冲) Reverse recovery energy	$I_F = 800 \text{ A}$, $-di_F/dt = 3300 \text{ A}/\mu\text{s}$ ($T_{vj}=125^{\circ}\text{C}$) $V_R = 2800 \text{ V}$ $V_{GE} = -15 \text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	E_{rec}	1200 2400		mJ mJ
结 - 外壳热阻 Thermal resistance, junction to case	每个二极管 / per diode		R_{thJC}		25,5	K/kW
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个二极管 / per diode $\lambda_{\text{Paste}} = 1 \text{ W}/(\text{m}\cdot\text{K})$ / $\lambda_{\text{grease}} = 1 \text{ W}/(\text{m}\cdot\text{K})$		R_{thCH}		21,0	K/kW
在开关状态下温度 Temperature under switching conditions			$T_{vj \text{ op}}$	-50	125	$^{\circ}\text{C}$

模块 / Module

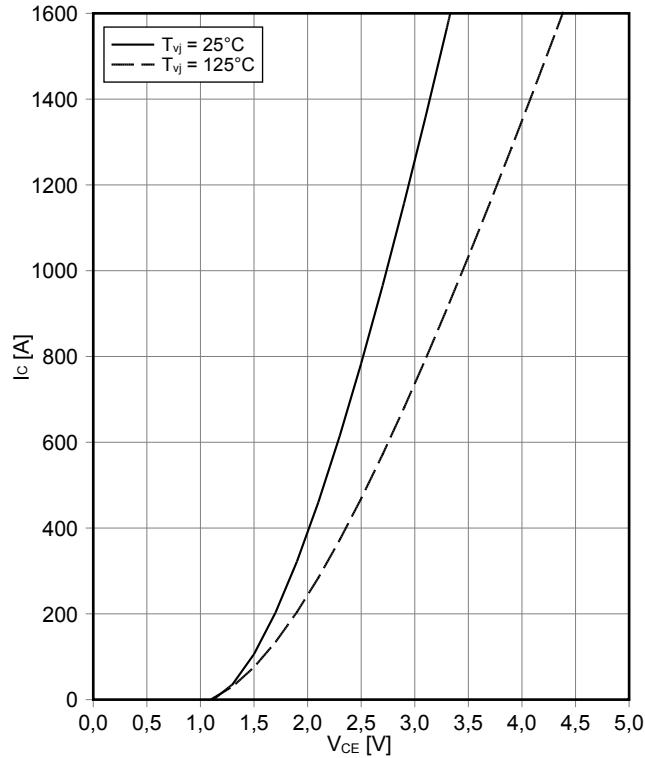
绝缘测试电压 Isolation test voltage	RMS, f = 50 Hz, t = 10 s	V _{ISOL}	10,4		kV
局部放电停止电压 Partial discharge extinction voltage	RMS, f = 50 Hz, Q _{PD} ≤ 10 pC	V _{ISOL}	3,5		kV
DC 稳定性 DC stability	T _{vj} = 25°C, 100 fit	V _{CE D}	3000		V
模块基板材料 Material of module baseplate			AISiC		
内部绝缘 Internal isolation	基本绝缘 (class 1, IEC 61140) basic insulation (class 1, IEC 61140)		AIN		
爬电距离 Creepage distance	端子至散热器 / terminal to heatsink 端子至端子 / terminal to terminal		56,0 56,0		mm
电气间隙 Clearance	端子至散热器 / terminal to heatsink 端子至端子 / terminal to terminal		26,0 26,0		mm
相对电痕指数 Comperative tracking index		CTI	> 600		
			min.	typ.	max.
杂散电感, 模块 Stray inductance module		L _{sCE}		20	nH
模块引线电阻, 端子-芯片 Module lead resistance, terminals - chip	T _c = 25°C, 每个开关 / per switch	R _{CC+EE'}		0,18	mΩ
储存温度 Storage temperature		T _{stg}	-55		125 °C
模块安装的安装扭矩 Mounting torque for modul mounting	螺丝 M6 根据相应的应用手册进行安装 Screw M6 - Mounting according to valid application note	M	4,25		5,75 Nm
端子联接扭矩 Terminal connection torque	螺丝 M4 根据相应的应用手册进行安装 Screw M4 - Mounting according to valid application note	M	1,8	-	2,1 Nm
	螺丝 M8 根据相应的应用手册进行安装 Screw M8 - Mounting according to valid application note		8,0	-	10 Nm
重量 Weight		G		1000	g

Das maximal zulässige du/dt, definiert zwischen 0,6 und 1×V_{ce}, beträgt 2400V/μs.
The maximum allowed dv/dt measured between 0,6 and 1×V_{ce} is 2400V/μs.

输出特性 IGBT, 逆变器 (典型)

output characteristic IGBT, Inverter (typical)

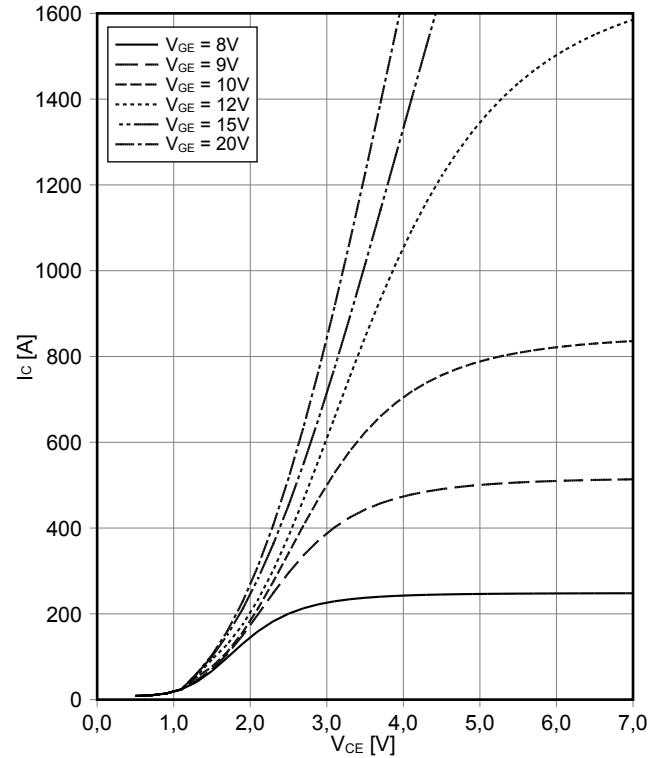
$I_C = f(V_{CE})$
 $V_{GE} = 15\text{ V}$



输出特性 IGBT, 逆变器 (典型)

output characteristic IGBT, Inverter (typical)

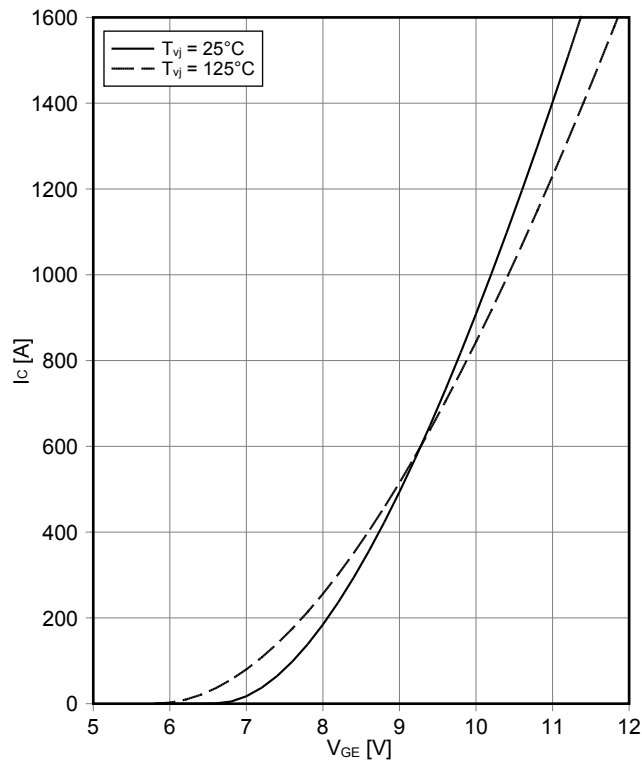
$I_C = f(V_{CE})$
 $T_{vj} = 125^\circ\text{C}$



传输特性 IGBT, 逆变器 (典型)

transfer characteristic IGBT, Inverter (typical)

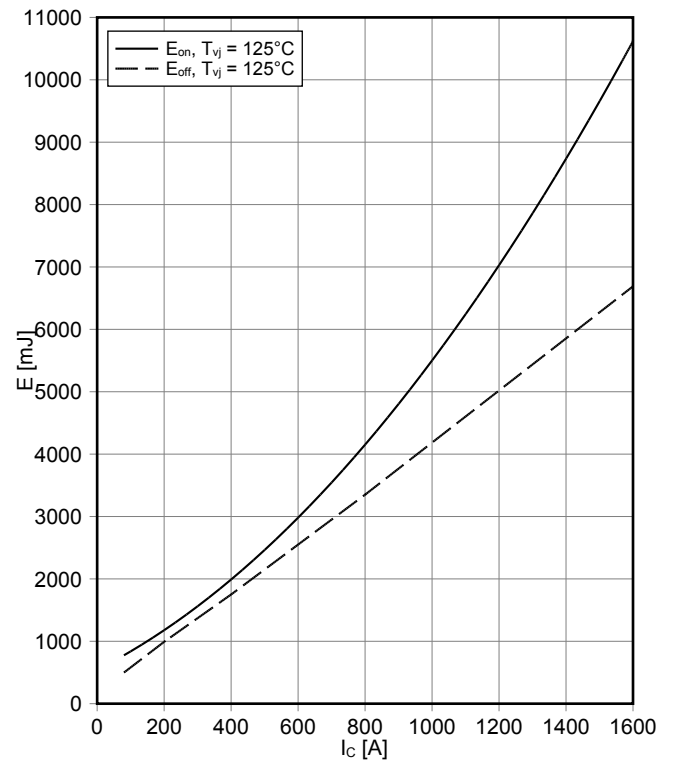
$I_C = f(V_{GE})$
 $V_{CE} = 20\text{ V}$



开关损耗 IGBT, 逆变器 (典型)

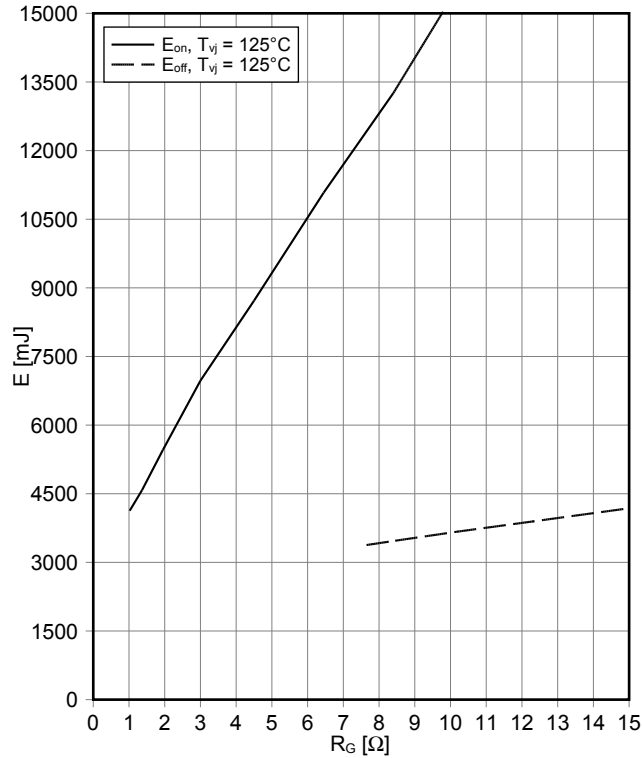
switching losses IGBT, Inverter (typical)

$E_{on} = f(I_C)$, $E_{off} = f(I_C)$
 $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 1\ \Omega$, $R_{Goff} = 7.5\ \Omega$, $V_{CE} = 2800\text{ V}$



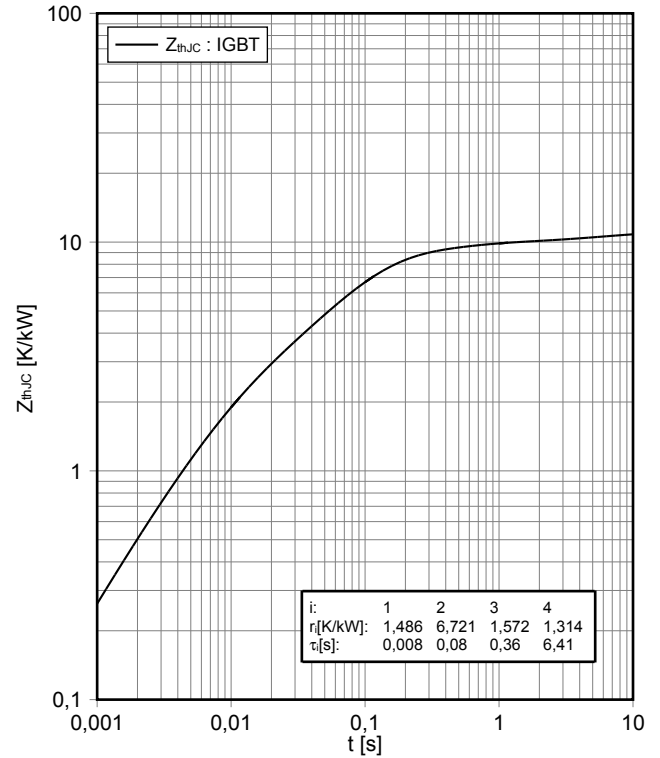
开关损耗 IGBT, 逆变器 (典型)
switching losses IGBT, Inverter (typical)

$E_{on} = f(R_G), E_{off} = f(R_G)$
 $V_{GE} = \pm 15 V, I_C = 800 A, V_{CE} = 2800 V$



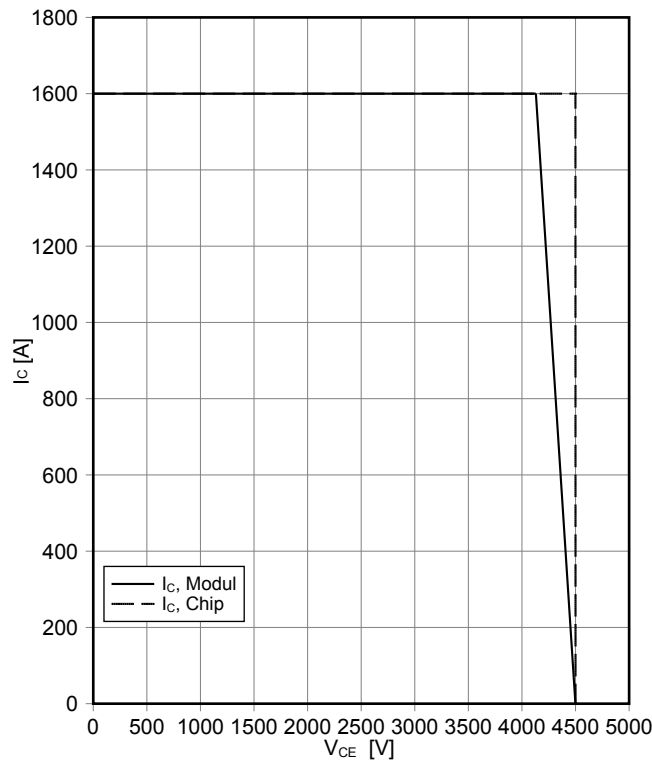
瞬态热阻抗 IGBT, 逆变器
transient thermal impedance IGBT, Inverter

$Z_{thJC} = f(t)$



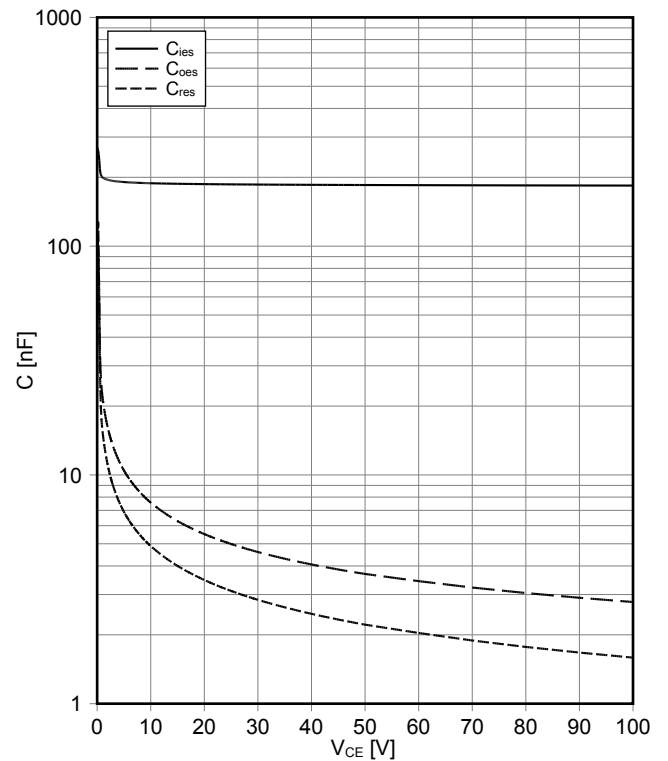
反偏安全工作区 IGBT, 逆变器 (RBSOA)
reverse bias safe operating area IGBT, Inverter (RBSOA)

$I_C = f(V_{CE})$
 $V_{GE} = \pm 15 V, R_{Goff} = 7.5 \Omega, T_{vj} = 125^\circ C$



电容特性 IGBT, 逆变器 (典型)
capacity characteristic IGBT, Inverter (typical)

$C = f(V_{CE})$
 $V_{GE} = 0 V, T_{vj} = 25^\circ C, f = 1 MHz$

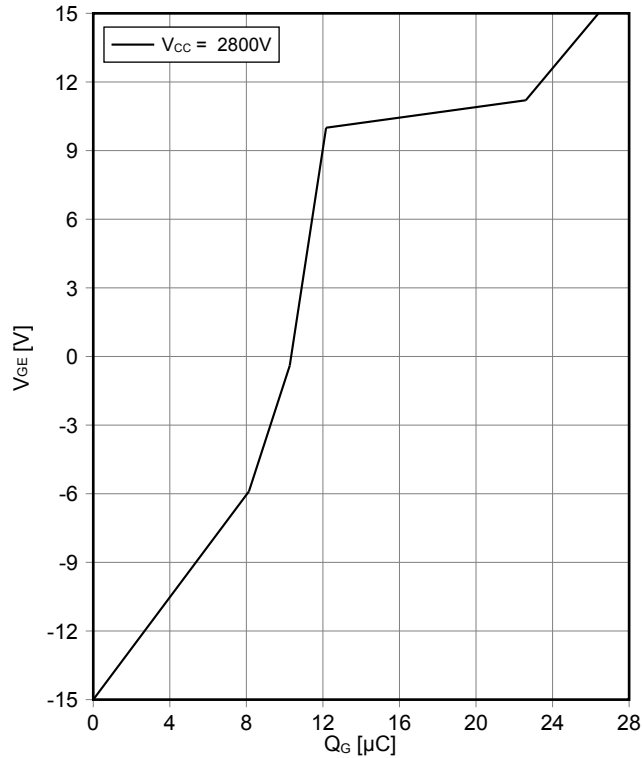


栅极电荷特性 IGBT, 逆变器 (典型)

gate charge characteristic IGBT, Inverter (typical)

$V_{GE} = f(Q_G)$

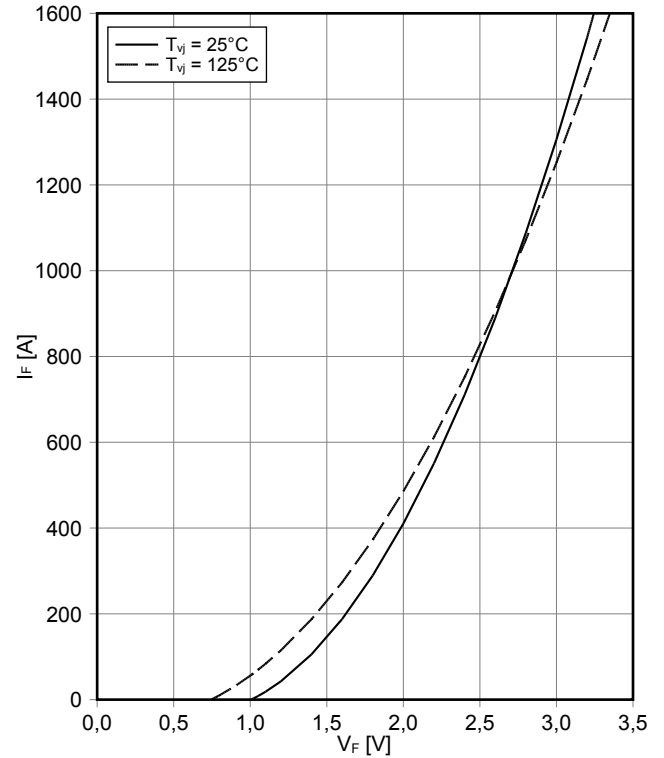
$I_C = 800 \text{ A}, T_{vj} = 25^\circ\text{C}$



正向偏压特性 二极管, 逆变器 (典型)

forward characteristic of Diode, Inverter (typical)

$I_F = f(V_F)$

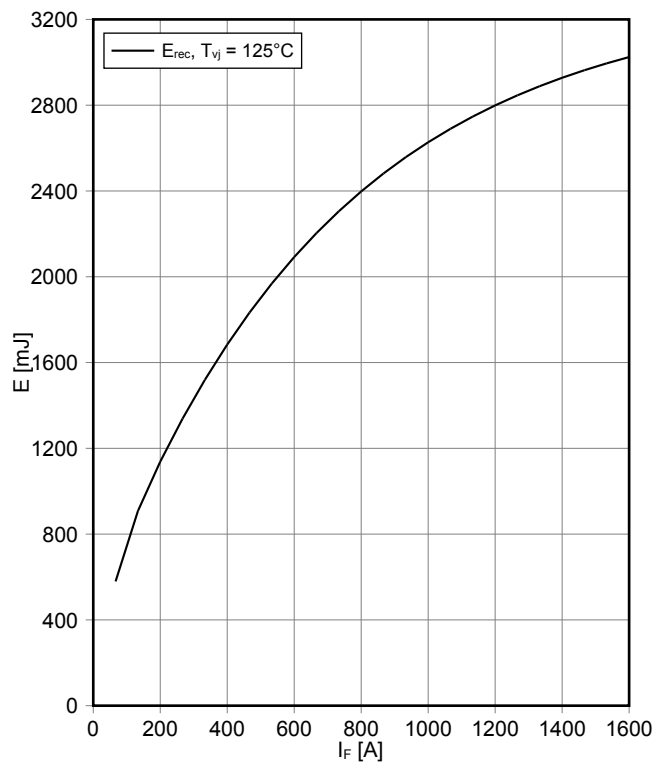


开关损耗 二极管, 逆变器 (典型)

switching losses Diode, Inverter (typical)

$E_{rec} = f(I_F)$

$-di_F/dt = 3300 \text{ A}/\mu\text{s}, V_{CE} = 2800 \text{ V}$

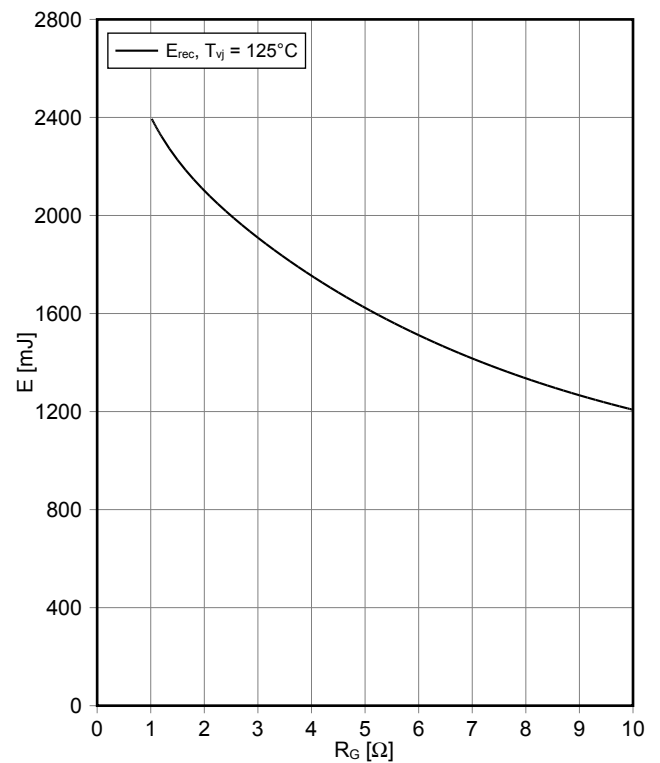


开关损耗 二极管, 逆变器 (典型)

switching losses Diode, Inverter (typical)

$E_{rec} = f(R_G)$

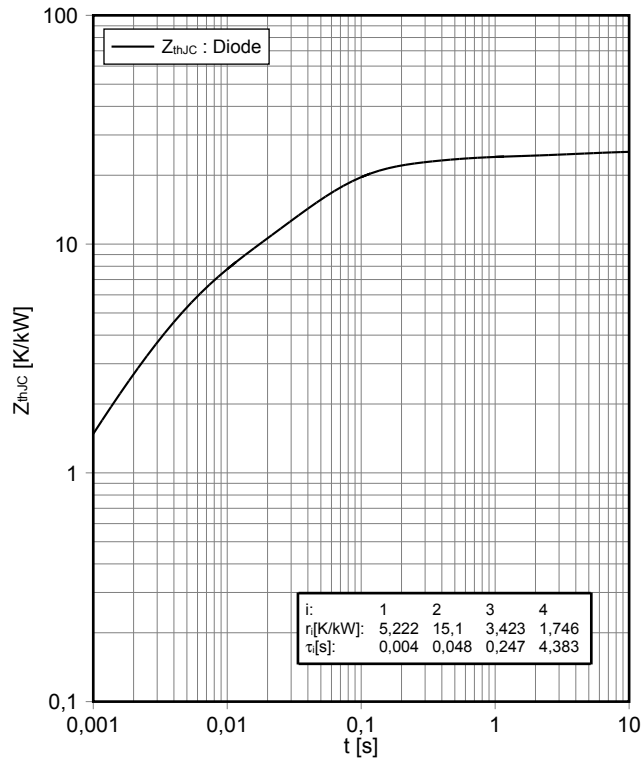
$I_F = 800 \text{ A}, V_{CE} = 2800 \text{ V}$



瞬态热阻抗 二极管,逆变器

transient thermal impedance Diode, Inverter

$Z_{thJC} = f(t)$

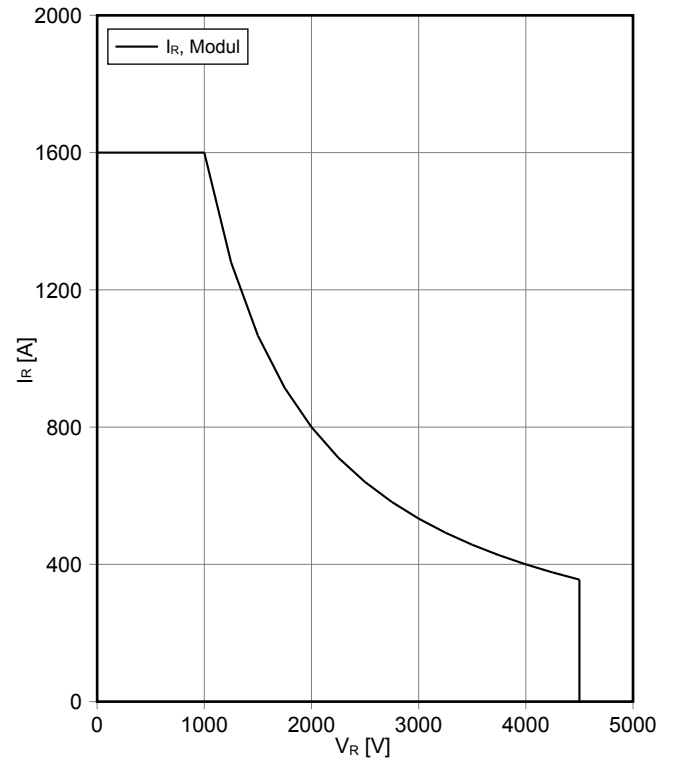


安全工作区 二极管,逆变器 (SOA)

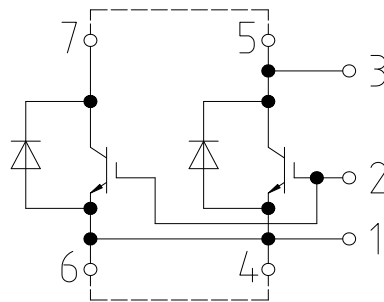
safe operation area Diode, Inverter (SOA)

$I_R = f(V_R)$

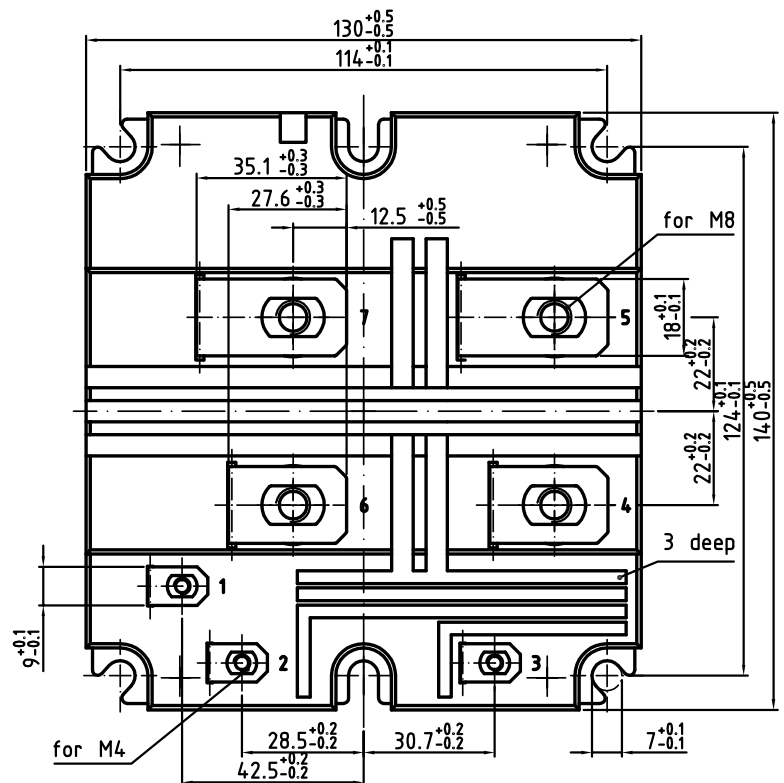
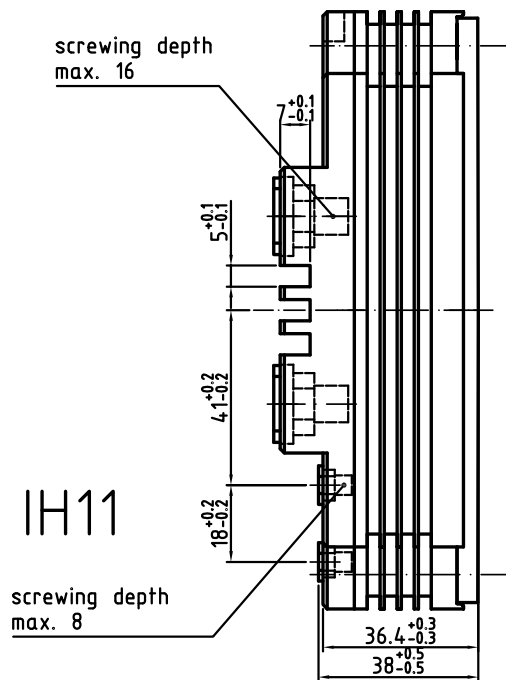
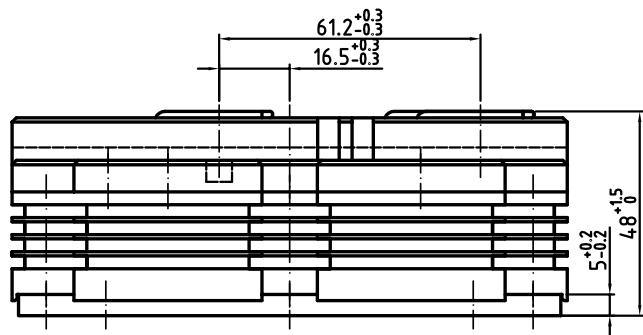
$T_{vj} = 125^{\circ}\text{C}$



接线图 / Circuit diagram



封装尺寸 / Package outlines



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